

EVERLIGHT

Technical Data Sheet

Opto Interrupter

ITR8102

Features

- Fast response time
- High analytic
- High sensitivity
- Pb free
- This product itself will remain within RoHS compliant version

Descriptions

The **ITR8102** consist of an infrared emitting diode and an NPN silicon phototransistor, encased side-by-side on converging optical axis in a black thermoplastic housing. The phototransistor receives radiation from the IR only. This is the normal situation. But when an object is in between, phototransistor could not receive the radiation.



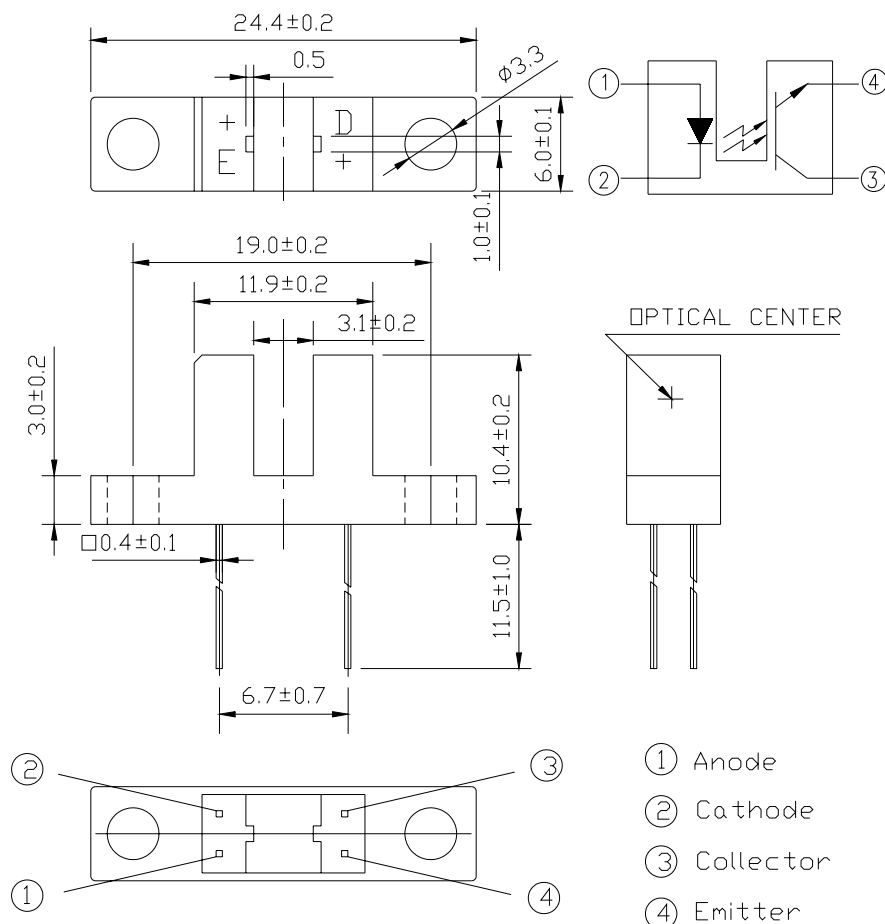
Applications

- Mouse Copier
- Switch Scanner
- Floppy disk driver
- Non-contact Switching
- For Direct Board

Device Selection Guide

Device No.	Chip Material	LENS COLOR
IR908-7C	GaAlAs	Water Clear
PT908-7C	Silicon	Water Clear

Package Dimensions



Notes:

1. All dimensions are in millimeters
2. Tolerances unless dimensions ± 0.2 mm
3. Lead spacing is measured where the lead emerge from the package
4. Above specification may be changed without notice. EVERLIGHT will reserve authority on material change for above specification
5. These specification sheets include materials protected under copyright of EVERLIGHT corporation. Please don't reproduce or cause anyone to reproduce them without EVERLIGHT's consent
6. When using this product, please observe the absolute maximum ratings and the instructions for use outlined in these specification sheets. EVERLIGHT assumes no responsibility for any damage resulting from use of the product which does not comply with the absolute maximum ratings and the instructions included in these specification sheets.

Absolute Maximum Ratings (Ta=25°C)

Parameter		Symbol	Ratings	Unit
Input	Power Dissipation at(or below) 25°C Free Air Temperature	Pd	75	mW
	Reverse Voltage	V _R	5	V
	Forward Current	I _F	50	mA
	Peak Forward Current (*1) Pulse width ≤ 100 μs, Duty cycle=1%	I _{FP}	1	A
Output	Collector Power Dissipation	P _C	75	mW
	Collector Current	I _C	30	mA
	Collector-Emitter Voltage	B V _{CEO}	30	V
	Emitter-Collector Voltage	B V _{ECO}	5	V
Operating Temperature		Topr	-25~+85	°C
Storage Temperature		Tstg	-40~+85	°C
Lead Soldering Temperature (*2) (1/16 inch form body for 5 seconds)		Tsol	260	°C

(*1) tw=100 μsec., T=10 msec. (*2) t=5 Sec

Electro-Optical Characteristics (Ta=25°C)

Parameter		Symbol	Min.	Typ.	Max.	Unit	Conditions
Input	Forward Voltage	V _F	---	1.2	1.5	V	I _F =20mA
	Reverse Current	I _R	---	---	10	μA	V _R =5V
	Peak Wavelength	λ _p	---	940	---	nm	I _F =20mA
	View Angle	2θ1/2	---	60	---	Deg	I _F =20mA
Output	Dark Current	I _{CEO}	---	---	100	nA	V _{CE} =20V, Ee=0mW/cm ²
	C-E Saturation Voltage	V _{CE(sat)}	---	---	0.4	V	I _C =2mA Ee=1mW/cm ²
Transfer Characteristics	Collect Current	I _{C(ON)}	0.9	---	15	mA	V _{CE} =5V I _F =20mA
	Rise time	t _r	---	15	---	μsec	V _{CE} =5V I _C =1mA R _L =1KΩ
	Fall time	t _f	---	15	---	μsec	

Typical Electrical/Optical/Characteristics Curves for IR

Fig. 1 Forward Current vs. Ambient Temperature

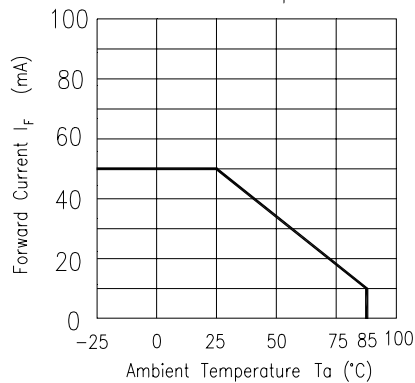


Fig. 2 Spectral Distribution

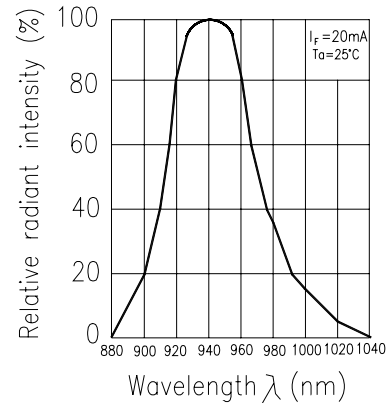


Fig. 3 Peak Emission Wavelength vs. Ambient Temperature

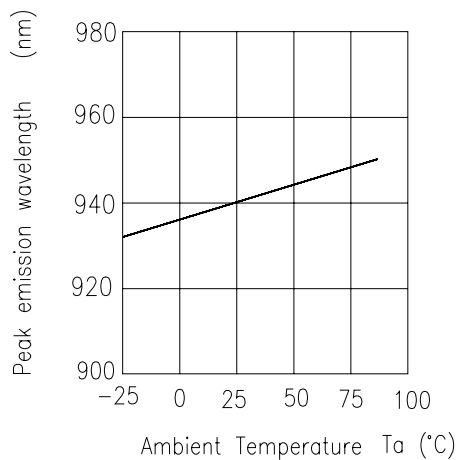


Fig. 4 Forward Current vs. Forward Voltage

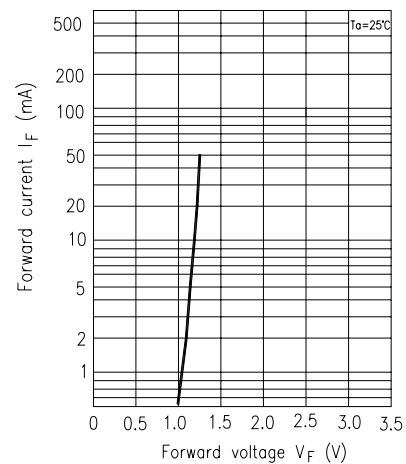


Fig. 5 Forward Voltage vs. Ambient Temperature

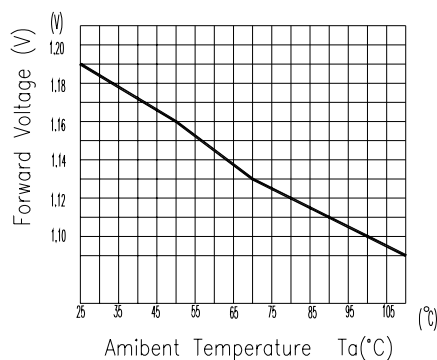
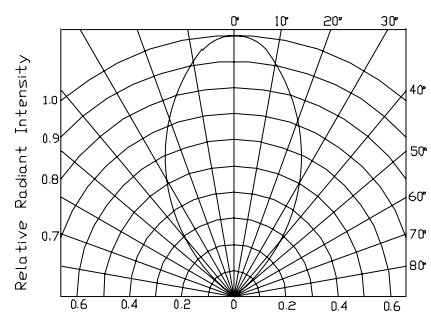
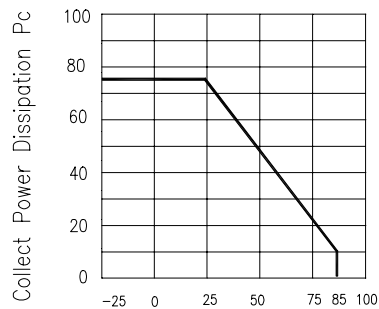


Fig. 6 Relative Radiant Intensity vs. Angular Displacement



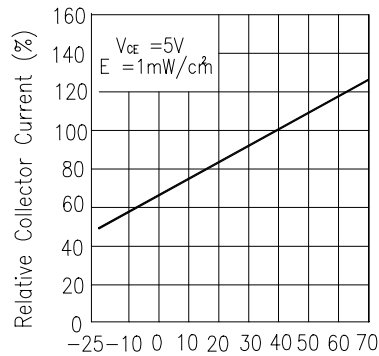
Typical Electrical/Optical/Characteristics Curves for PT

Fig.1 Collector Power Dissipation vs. Ambient Temperature



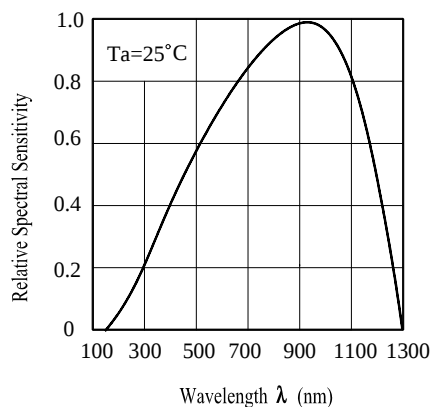
Ambient Temperature T_a (°C)

Fig. 3 Relative Collector Current vs. Ambient Temperature



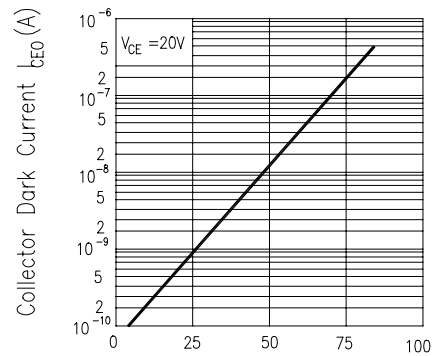
Ambient Temperature T_a (°C)

Fig.5 Spectral Sensitivity



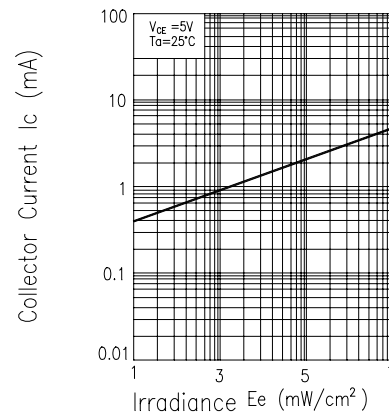
Wavelength λ (nm)

Fig.2 Collector Dark Current vs. Ambient Temperature



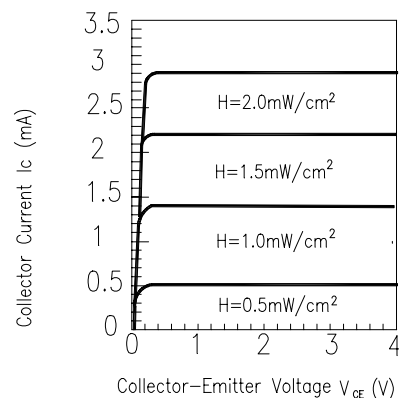
Ambient Temperature T_a (°C)

Fig.4 Collector Current vs. Irradiance



Irradiance E_e (mW/cm²)

Fig.6 Collector Current vs. Collector-Emitter Voltage



Collector-Emitter Voltage V_{ce} (V)

Reliability Test Item And Condition

The reliability of products shall be satisfied with items listed below.

Confidence level : 90%

LTPD : 10%

NO.	Item	Test Condition	Test Hours/ Cycle	Sample Size	Failure Judgement Criteria	Ac/Re
1	Solder Heat	TEMP : 260°C ± 5 °C	10sec	22 pcs	$I_R \geq U \times 2$ $E_e \leq L \times 0.8$ $V_F \geq U \times 1.2$ U :Upper specification limit L :Lower specification limit	0/1
2	Temperature Cycle	H : +100°C 15 mins $\updownarrow$ 5 min L : -40°C 15 min	300 cycle	22 pcs		0/1
3	Thermal Shock	H : +100°C 5 min $\updownarrow$ 10 sec L : -10°C 5 min	300 cycle	22 pcs		0/1
4	High Temperature Storage	TEMP. : +100°C	1000 hrs	22 pcs		0/1
5	Low Temperature Storage	TEMP. : -40°C	1000 hrs	22 pcs		0/1
6	DC Operating Life	$V_{CE}=5V$ $I_F=20mA$	1000 hrs	22 pcs		0/1
7	High Temperature / High Humidity	85°C / 85% R.H.	1000 hrs	22 pcs		0/1

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